PTO/SB/084(10:01)
Approved for use through 10/31/2002, ONØ 651-0031
US Pased & Trabaser's Office; U.S. DEPARTMENT OF COLORERCE

Substitute for form 1449A/PTO	Complete if Known	required to respond to a collection of information unless it contains a valid QMG control number
INFORMATION DISCLOSURE	Application Number	10/634,174
STATEMENT BY APPECANT	Filing Date	August 5, 2003
9 2005	First Named Inventor	Forbes, Leonard
JUL 18 2005 7	Group Art Unit	2823
	Examiner Name	Garcia, Joannie
Sheet 1 of 1	Attorney Docket No: 1	303.102US1

		US P	ATENT DOCUMENTS	
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date If Appropriate
JAG	US-4,962,051	10/09/1990	Liaw, H. M.	11/18/1988
TAG	US-5,735,949	04/07/1998	Mantl, S., et al.	09/13/1991
- AC	US-6,825,102	11/30/2004	Bedell, S. W., et al.	09/18/2003

		FOREIGN PATENT	DOCUMENTS	
Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	T²

	OTHE	R DOCUMENTS NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	Tr
SAG		KAL, S., et al., "Strained Silicon-SiGe Devices Using Germanium Implantation", IETE Journal of Research, 43 (2-3), (Mar. 1997), 185-192	
JK		XIAO, Q., et al., "Preparation of thin Strained Si Film by Low Temperature Ge Ion Implantation and High Temperature Annealing", Solid-State and Integrated Circuits Technology, 2004. Proceedings 7th Int'l Conf., 3(3), (Oct. 18, 2004), 2163-2166	

EXAMINER

in DATE CONSIDERED September 29,2005

Substitute for form 1449A/PTO
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary) COPY

Application Number	10/634,174	
Filing Date	August 5, 2003	
First Named Inventor	Forbes, Leonard	
Group Art Unit	2823	
Examiner Name	Garcia, Joannie	

Sheet	1	of	1
-------	---	----	---

Attorney Docket No: 1303.102US1

		US PATE	NT DOCUMENTS	
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date if Appropriate
JAG	US-2004/0171196-A1	09/02/2004	Walitzki, H J.	08/07/2003
JAE	US-2004/0173798	09/09/2004	Forbes, Leonard	03/05/2003
JAC	US-2004/0214366-A1	10/28/2004	Segal, B M., et al.	05/20/2004
JAK	US-2004/0217352-A1	11/04/2004	Forbes, L.	04/29/2003
JAZ	US-2004/0217391	11/04/2004	Forbes, Leonard	04/29/2003
JAC	US-2004/0224480-A1	11/11/2004	Forbes, L.	05/07/2003
124	US-2004/0232422-A1	11/25/2004	Forbes, L.	05/21/2003
SK,	US-2004/0232487-A1	11/25/2004	Forbes, L.	05/21/2003
SKS	US-2004/0232488-A1	11/25/2004	Forbes, L.	05/21/2003
SAC	US-2004/0235264-A1	11/25/2004	Forbes, L.	05/21/2003
SK	US-2005/0017273-A1	01/27/2005	Forbes, L., et al.	07/21/2003
JAC	US-2005/0020094-A1	01/27/2005	Forbes, L., et al.	07/21/2003
JAK	US-2005/0023529-A1	02/03/2005	Forbes, L.	08/31/2005
JAK	US-2005/0023612-A1	02/03/2005	Forbes, L.	08/31/2004
JK	US-2005/0023616-A1	02/03/2005	Forbes, L.	08/31/2004
JAC	US-2005/0029683-A1	02/10/2005	Forbes, L., et al.	08/31/2004
JAK	US-2005/0032296-A1	02/10/2005	Forbes, L.	08/31/2004
JAG	US-4,523,975	06/18/1985	Groves, C. K., et al.	04/28/1982
184	US-5,854,501	12/29/1998	Kao, D. Y.	11/20/1995
DAG.	US-5,877,070	03/02/1999	Goesele, U. M., et al.	05/31/1997
J)K	US-5,987,200	11/16/1999	Fleming, D. A., et al.	10/27/1997
SAC	US-6,103,598	08/15/2000	Yamagata, K., et al.	07/11/1996
JAC	US-6,143,628	11/07/2000	Sato, N., et al.	03/25/1998
JAG	US-6,162,657	12/19/2000	Schiele, I., et al.	05/11/1999
DAG.	US-6,180,487	01/30/2001	Lin, M.	10/25/1999
286	US-6,328,796	12/11/2001	Kub, F. J., et al.	02/01/1999
JAG	US-6,455,397	09/24/2002	Belford, Rona E.	11/09/2000
JAC	US-6,486,008	11/26/2002	Lee, T.	08/01/2000
DK	US-6,497,763	12/24/2002	Kub, F. J., et al.	01/19/2001
JAK	US-6,514,836	02/04/2003	Belford, Rona E.	06/04/2001
JAG	US-6,656,822	12/02/2003	Doyle, B. S., et al.	06/28/1999
JK.	US-6,689,671	02/10/2004	Yu, B, et al.	05/22/2002
SKG.	US-6,812,508	11/02/2004	Fukumi, M.	11/27/2001

	OTHE	R DOCUMENTS NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No 1	include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	7
SK		LU, X., et al., "SiGe and SiGeC Surface Alloy Formation Using High-Dose Implantation and Solid Phase Epitaxy", <u>Proceedings of the 11th International Conference on Ion Implantation Technology</u> , Austin, TX, (1997), 686-689	

EXAMINER

banne

DATE CONSIDERED Suplanta 29 2005